

**isc N-Channel MOSFET Transistor**

**IRFP260N, IIRFP260N**

**• FEATURES**

- Static drain-source on-resistance:  
 $R_{DS(on)} \leq 40m\Omega$
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**• DESCRIPTION**

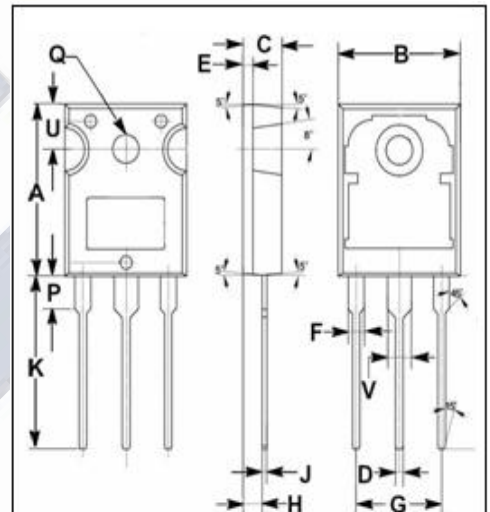
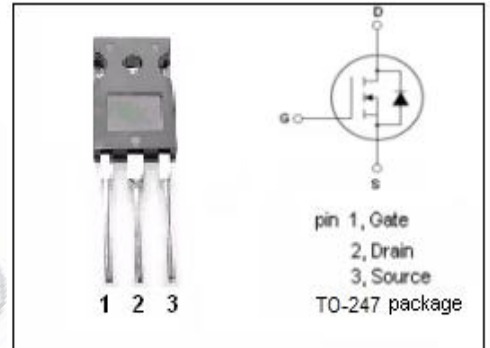
- Fast switching
- Fully Avalanche Rated

**• ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage	200	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-Continuous	50	A
I <sub>DM</sub>	Drain Current-Single Pulsed	200	A
P <sub>D</sub>	Total Dissipation @T <sub>c</sub> =25°C	300	W
T <sub>j</sub>	Max. Operating Junction Temperature	175	°C
T <sub>stg</sub>	Storage Temperature	-55~175	°C

**• THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th(j-c)</sub>	Channel-to-case thermal resistance	0.5	°C/W
R <sub>th(j-a)</sub>	Channel-to-ambient thermal resistance	40	°C/W



DIM	mm	
	MIN	MAX
A	19.80	20.20
B	15.40	15.80
C	4.90	5.10
D	0.90	1.10
E	1.40	1.60
F	1.90	2.10
G	10.80	11.00
H	2.40	2.60
J	0.50	0.70
K	19.50	20.50
P	3.90	4.10
Q	3.30	3.50
U	5.20	5.40
V	2.90	3.10

**isc N-Channel MOSFET Transistor**
**IRFP260N, IIRFP260N**
**ELECTRICAL CHARACTERISTICS**

 T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =250 μ A	200			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; I <sub>D</sub> =250 μ A	2.0		4.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =28A			40	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V			±0.1	μ A
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =200V; V <sub>GS</sub> = 0V			25	μ A
V <sub>SD</sub>	Diode forward voltage	I <sub>S</sub> =28A, V <sub>GS</sub> = 0V			1.3	V